

SINGLE INVERTER (OPEN DRAIN)

- HIGH SPEED: $t_{PD} = 3.7$ ns (TYP.) at $V_{CC} = 5$ V
- LOW POWER DISSIPATION: $I_{CC} = 1\mu A(MAX.)$ at $T_A=25^{\circ}C$
- HIGH NOISE IMMUNITY: V_{NIH} = V_{NIL} = 28% V_{CC} (MIN.)
- POWER DOWN PROTECTION ON INPUT
- OPERATING VOLTAGE RANGE: V_{CC}(OPR) = 2V to 5.5V
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

The 74V1G05 is an advanced high-speed CMOS SINGLE INVERTER (OPEN DRAIN) fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology.

The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output.

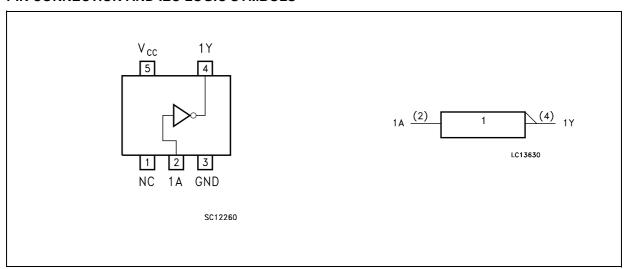


ORDER CODES

PACKAGE	T&R
SOT23-5L	74V1G05STR
SOT323-5L	74V1G05CTR

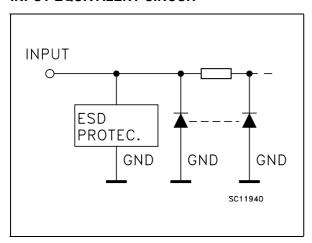
Power down protection is provided on input and 0 to 7V can be accepted on input with no regard to the supply voltage. This device can be used to interface 5V to 3V.

PIN CONNECTION AND IEC LOGIC SYMBOLS



April 2004 1/9

INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN N°	SYMBOL	NAME AND FUNCTION
1	NC	Not Connected
2	1A	Data Input
4	1Y	Data Output
3	GND	Ground (0V)
5	V _{CC}	Positive Supply Voltage

TRUTH TABLE

A	Y
L	Z
Н	L

Z: High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 5.5	V
V _I	Input Voltage	0 to 5.5	V
Vo	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) (V _{CC} = 3.3 ± 0.3 V) (V _{CC} = 5.0 ± 0.5 V)	0 to 100 0 to 20	ns/V ns/V

¹⁾ V_{IN} from 30% to 70% of V_{CC}

2/9

DC SPECIFICATIONS

		1	est Condition				Value				
Symbol	Parameter	v _{cc}		T	T _A = 25°C			85°C	-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	3.0 to 5.5		0.7V _{CC}			0.7V _{CC}		0.7V _{CC}		V
V _{IL}	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	3.0 to 5.5				0.3V _{CC}		0.3V _{CC}		0.3V _{CC}	V
V _{OL}	Low Level Output	2.0	I _O =50 μA		0.0	0.1		0.1		0.1	
	Voltage	3.0	I _O =50 μA		0.0	0.1		0.1		0.1	
		4.5	I _O =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I _O =4 mA			0.36		0.44		0.55	
		4.5	I _O =8 mA			0.36		0.44		0.55	
I _{OZ}	High Impedance Output Leakage Current	5.5	$V_I = V_{IH} \text{ or } V_{IL}$ $V_O = V_{CC} \text{ or GND}$			± 0.25		± 2.5		± 5	μΑ
l _l	Input Leakage Current	0 to 5.5	V _I = 5.5V or GND			± 0.1		± 1		± 1	μΑ
I _{CC}	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10		20	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$)

		1	Test Condition		Value							
Symbol Parameter		V _{CC}	V _{CC} C _L		T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit
		V _{CC}) (pF)	-	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{PZL}	Propagation Delay	3.3 ^(*)	15			4.8	7.7	1.0	9.0	1.0	10.0	
	Time	3.3 ^(*)	50			5.3	8.5	1.0	10.0	1.0	11.0	nc
		5.0 ^(**)	15			3.7	5.5	1.0	6.5	1.0	7.5	ns
		5.0 ^(**)	50			4.2	7.5	1.0	8.5	1.0	9.5	
t _{PLZ} Propagation Delay	3.3 ^(*)	50			7.5	10.5	1.0	11.5	1.0	12.5	ns	
	Time	5.0 ^(**)	50			4.7	7.5	1.0	8.5	1.0	9.5	115

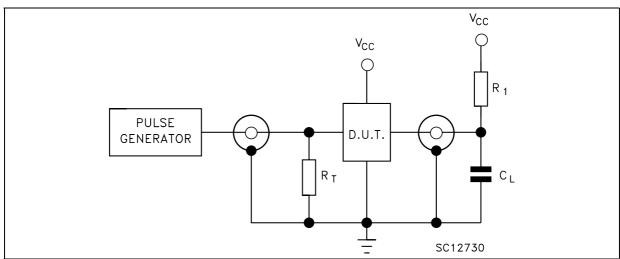
^(*) Voltage range is 3.3V ± 0.3V (**) Voltage range is 5.0V ± 0.5V

CAPACITIVE CHARACTERISTICS

		Test Condition	Value							
Symbol	Parameter		Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance			4	10		10		10	pF
C _{OUT}	Output Capacitance			5	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)			3						pF

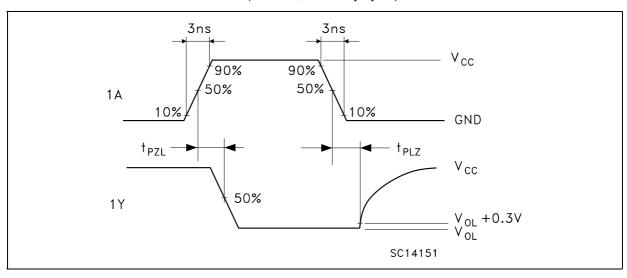
¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

TEST CIRCUIT



 C_L = 15/50pF or equivalent (includes jig and probe capacitance) R_1 = 1K Ω or equivalent R_T = Z_{OUT} of pulse generator (typically 50 Ω)

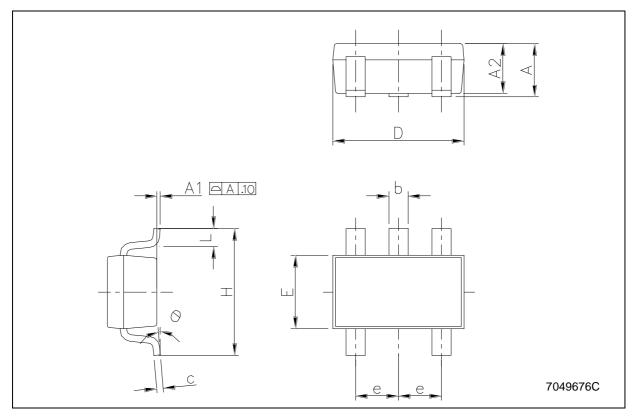
WAVEFORM: PROPAGATION DELAY (f=1MHz; 50% duty cycle)



47/ 4/9

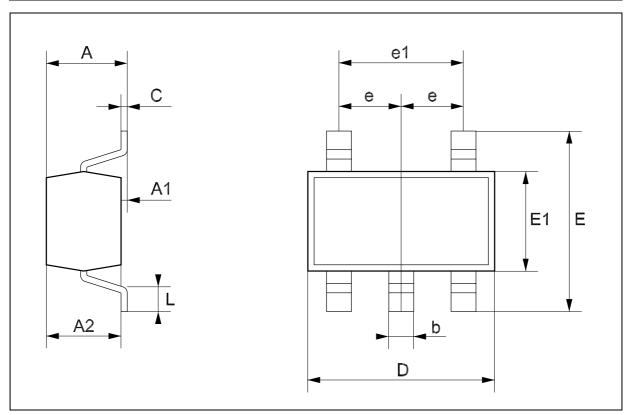
SOT23-5L MECHANICAL DATA

DIM		mm.		mils			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А	0.90		1.45	35.4		57.1	
A1	0.00		0.10	0.0		3.9	
A2	0.90		1.30	35.4		51.2	
b	0.35		0.50	13.7		19.7	
С	0.09		0.20	3.5		7.8	
D	2.80		3.00	110.2		118.1	
E	1.50		1.75	59.0		68.8	
е		0.95			37.4		
Н	2.60		3.00	102.3		118.1	
L	0.10		0.60	3.9		23.6	



SOT323-5L MECHANICAL DATA

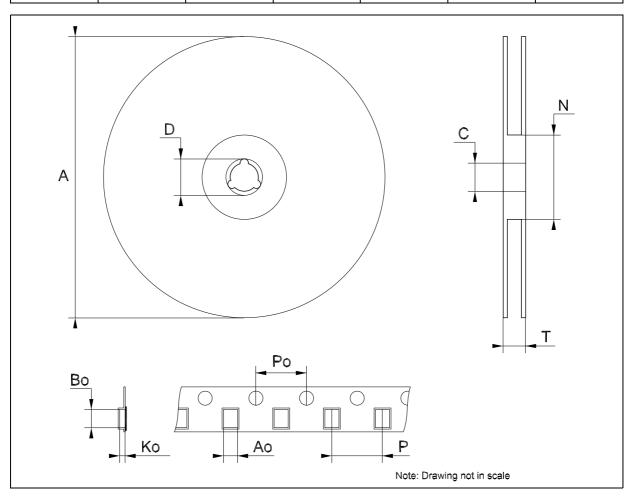
DIM		mm.				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	0.80		1.10	31.5		43.3
A1	0.00		0.10	0.0		3.9
A2	0.80		1.00	31.5		39.4
b	0.15		0.30	5.9		11.8
С	0.10		0.18	3.9		7.1
D	1.80		2.20	70.9		86.6
E	1.80		2.40	70.9		94.5
E1	1.15		1.35	45.3		53.1
е		0 .65			25.6	
e1		1.3			51.2	
L	0.10		0.30	3.9		11.8



6/9

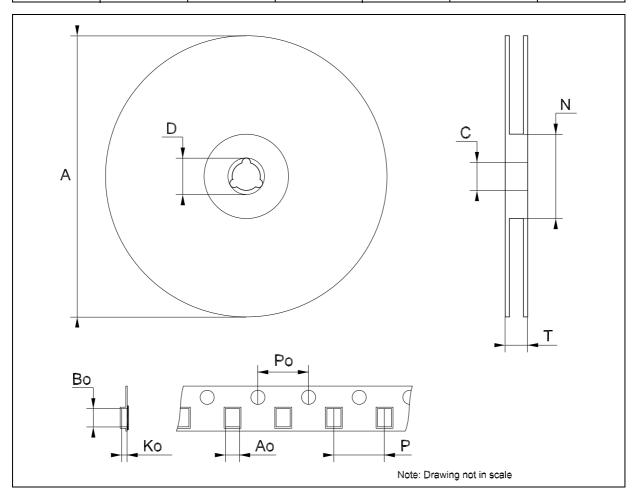
Tape & Reel SOT23-xL MECHANICAL DATA

DIM		mm.			inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			180			7.086		
С	12.8	13.0	13.2	0.504	0.512	0.519		
D	20.2			0.795				
N	60			2.362				
Т			14.4			0.567		
Ao	3.13	3.23	3.33	0.123	0.127	0.131		
Во	3.07	3.17	3.27	0.120	0.124	0.128		
Ко	1.27	1.37	1.47	0.050	0.054	0.0.58		
Po	3.9	4.0	4.1	0.153	0.157	0.161		
Р	3.9	4.0	4.1	0.153	0.157	0.161		



Tape & Reel SOT323-xL MECHANICAL DATA

DIM		mm.		inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А	175	180	185	6.889	7.086	7.283	
С	12.8	13	13.2	0.504	0.512	0.519	
D	20.2			0.795			
N	59.5	60	60.5		2.362		
Т			14.4			0.567	
Ao		2.25			0.088		
Во		2.7			0.106		
Ko		1.2			0.047		
Ро	3.9	4	4.1	0.153	0.157	0.161	
Р	3.8	4	4.2	0.149	0.157	0.165	



8/9

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics All other names are the property of their respective owners

© 2004 STMicroelectronics - All Rights Reserved STMicroelectronics GROUP OF COMPANIES

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

http://www.st.com

